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DATA SHEET
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Field Stop Trench IGBT

650 V, 75 A

AFGHL75T65SQDT

Using the novel field stop 4th generation IGBT technology and the Stealth Diode technology, AFGHL75T65SQDT offers the optimum performance with both low conduction and switching losses for a high efficiency operation in various applications, especially totem pole bridgeless PFC and DCDC block as well.

Features

- AEC−Q101 Qualified
- Maximum Junction Temperature: T_J = 175°C
- Positive Temperature Co−efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(Sat)}$ = 1.6 V (Typ.) @ I_C = 75 A
- 100% of the Parts are Tested for I_{LM} (Note 2)
- Fast Switching
- Tight Parameter Distribution
- RoHS Compliant

Typical Applications

- Automotive HEV−EV Onboard Chargers
- Automotive HEV−EV DC−DC Converters
- Totem Pole Bridgeless PFC

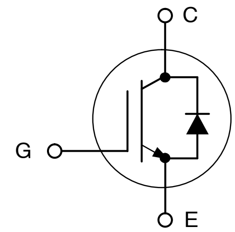
MAXIMUM RATINGS

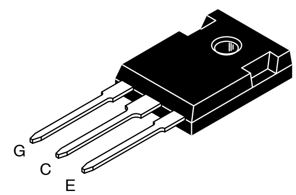
Rating		Symbol	Value	Unit
Collector−to−Emitter Voltage		V_{CES}	650	V
Gate−to−Emitter Voltage Transient Gate−to−Emitter Voltage		V_{GES}	±20 ±30	V
Collector Current (Note 1)	@ T_C = 25°C @ T_C = 100°C	I_C	80 75	A
Pulsed Collector Current (Note 2)		I_{LM}	300	A
Pulsed Collector Current (Note 3)		I_{CM}	300	A
Diode Forward Current	@ T_C = 25°C @ T_C = 100°C	I_F	80 75	A
Pulsed Diode Maximum Forward Current		$I_{FM(2)}$	300	A
Maximum Power Dissipation	@ T_C = 25°C @ T_C = 100°C	P_D	375 188	W
Operating Junction / Storage Temperature Range		T_J, T_{STG}	−55 to +175	°C
Maximum Lead Temp. for Soldering Purposes, 1/8″ from case for 5 seconds		T_L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Value limit by bond wire
2. V_{CC} = 400 V, V_{GE} = 15 V, I_C = 300 A, R_G = 17 Ω, Inductive Load
3. Repetitive Rating: pulse width limited by max. Junction temperature

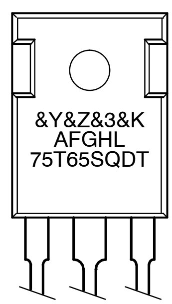
75 A, 650 V
V_{CESat} = 1.6 V





TO−247−3L
CASE 340CX

MARKING DIAGRAM



&Y = **onsemi** Logo
&Z = Assembly Plant Code
&3 = 3−Digit Data Code
&K = 2−Digit Lot Traceability Code
AFGHL75T65SQDT = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
AFGHL75T65SQDT	TO−247−3L	30 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction−to−case, for IGBT	$R_{\theta JC}$	0.4	°C/W
Thermal resistance junction−to−case, for Diode	$R_{\theta JC}$	0.65	°C/W
Thermal resistance junction−to−ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 1 mA	BV_{CES}	650	–	–	V
Temperature Coefficient of Breakdown Voltage	V_{GE} = 0 V, I_C = 1 mA	$\frac{\Delta BV_{CES}}{\Delta T_J}$	–	0.6	–	V/°C
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 650 V	I_{CES}	–	–	250	μA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	–	–	±400	nA
ON CHARACTERISTICS						
Gate−emitter threshold voltage	$V_{GE} = V_{CE}$, I_C = 75 mA	$V_{GE(th)}$	3.4	4.9	6.4	V
Collector−emitter saturation voltage	V_{GE} = 15 V, I_C = 75 A V_{GE} = 15 V, I_C = 75 A, T_J = 175°C	$V_{CE(sat)}$	– –	1.6 1.95	2.1 –	V
DYNAMIC CHARACTERISTICS						
Input capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	C_{ies}	–	4617	–	pF
Output capacitance		C_{oes}	–	152	–	
Reverse transfer capacitance		C_{res}	–	13	–	
Gate charge total	V_{CE} = 400 V, I_C = 75 A, V_{GE} = 15 V	Q_g	–	136	–	nC
Gate−to−emitter charge		Q_{ge}	–	25	–	
Gate−to−collector charge		Q_{gc}	–	32	–	
SWITCHING CHARACTERISTICS, INDUCTIVE LOAD						
Turn−on delay time	T_C = 25°C, V_{CC} = 400 V, I_C = 37.5 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load	$t_{d(on)}$	–	21	–	ns
Rise time		t_r	–	16	–	
Turn−off delay time		$t_{d(off)}$	–	113	–	
Fall time		t_f	–	8	–	
Turn−on switching loss		E_{on}	–	0.77	–	mJ
Turn−off switching loss		E_{off}	–	0.23	–	
Total switching loss		E_{ts}	–	1.0	–	
Turn−on delay time	T_C = 25°C, V_{CC} = 400 V, I_C = 75 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load	$t_{d(on)}$	–	24	–	ns
Rise time		t_r	–	44	–	
Turn−off delay time		$t_{d(off)}$	–	106	–	
Fall time		t_f	–	68	–	
Turn−on switching loss		E_{on}	–	2.12	–	mJ
Turn−off switching loss		E_{off}	–	1.14	–	
Total switching loss		E_{ts}	–	3.26	–	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS, INDUCTIVE LOAD						
Turn−on delay time	T_C = 175°C, V_{CC} = 400 V, I_C = 37.5 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load	$t_{d(on)}$	–	20	–	ns
Rise time		t_r	–	19	–	
Turn−off delay time		$t_{d(off)}$	–	124	–	
Fall time		t_f	–	7.7	–	
Turn−on switching loss		E_{on}	–	1.52	–	mJ
Turn−off switching loss		E_{off}	–	0.43	–	
Total switching loss		E_{ts}	–	1.95	–	
Turn−on delay time	T_C = 175°C, V_{CC} = 400 V, I_C = 75 A, R_G = 4.7 Ω, V_{GE} = 15 V, Inductive Load	$t_{d(on)}$	–	24	–	ns
Rise time		t_r	–	45	–	
Turn−off delay time		$t_{d(off)}$	–	114	–	
Fall time		t_f	–	76	–	
Turn−on switching loss		E_{on}	–	3.32	–	mJ
Turn−off switching loss		E_{off}	–	1.42	–	
Total switching loss		E_{ts}	–	4.74	–	
DIODE CHARACTERISTICS						
Diode Forward Voltage	I_F = 75 A, T_C = 25°C	V_{FM}	–	1.65	2.1	V
	I_F = 75 A, T_C = 175°C		–	1.55	–	
Reverse Recovery Energy	I_F = 75 A, dI_F/dt = 200 A/s, T_C = 175°C	E_{rec}	–	150	–	μJ
Diode Reverse Recovery Time	I_F = 75 A, dI_F/dt = 200 A/s, T_C = 25°C	T_{rr}	–	75	–	ns
	I_F = 75 A, dI_F/dt = 200 A/s, T_C = 175°C		–	328	–	
Diode Reverse Recovery Charge	I_F = 75 A, dI_F/dt = 200 A/s, T_C = 25°C	Q_{rr}	–	173	–	nC
	I_F = 75 A, dI_F/dt = 200 A/s, T_C = 175°C		–	2193	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

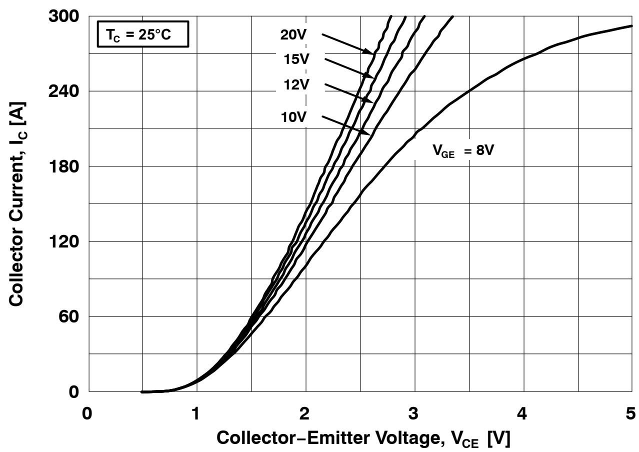


Figure 1. Typical Output Characteristics (T_J = 25°C)

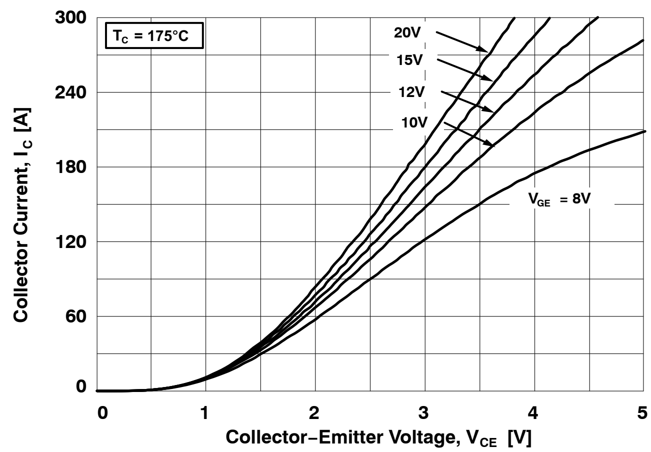


Figure 2. Typical Output Characteristics (T_J = 175°C)

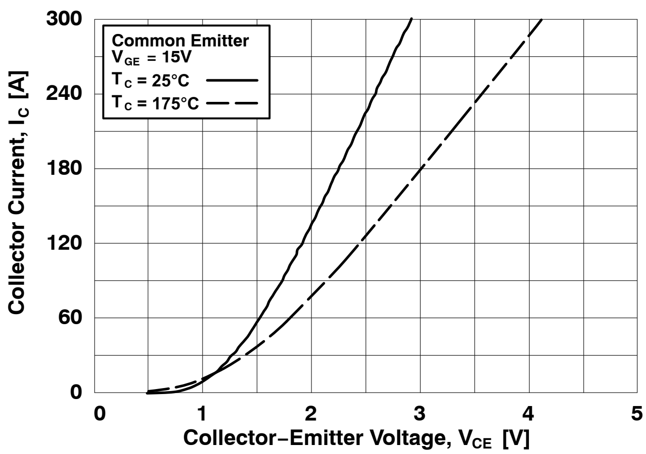


Figure 3. Typical Saturation Voltage Characteristics

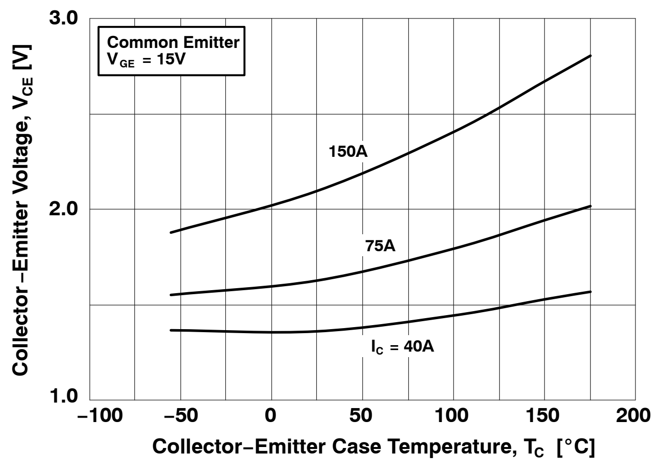


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

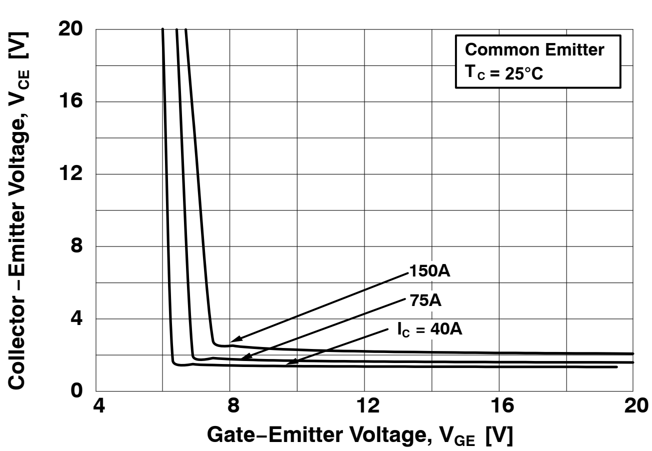


Figure 5. Saturation Voltage vs. V_{GE} (T_J = 25°C)

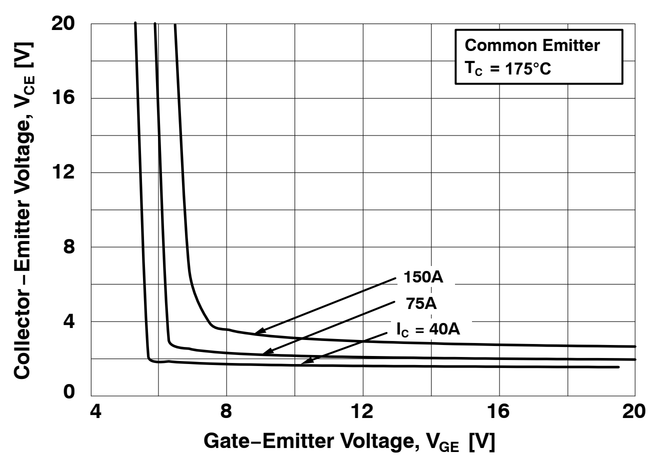


Figure 6. Saturation Voltage vs. V_{GE} (T_J = 175°C)

TYPICAL CHARACTERISTICS (continued)

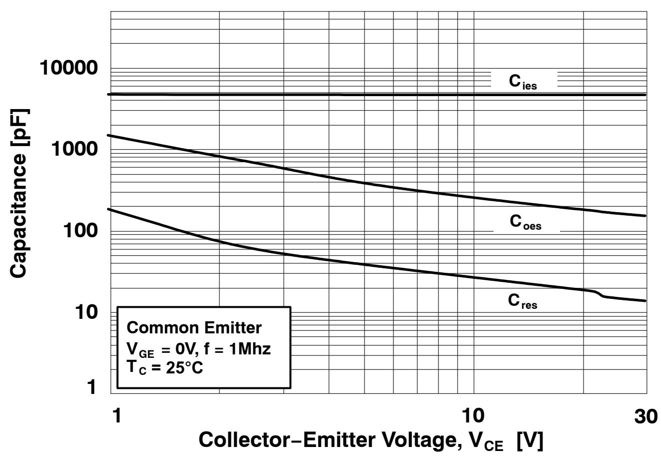


Figure 7. Capacitance Characteristics

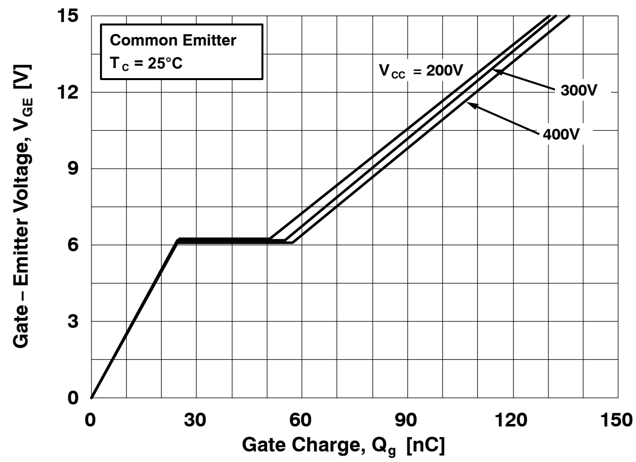


Figure 8. Gate Charge Characteristics

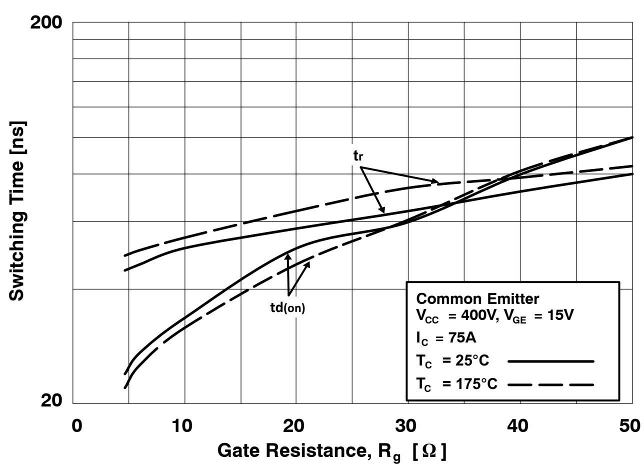


Figure 9. Turn−On Characteristics vs. Gate Resistance

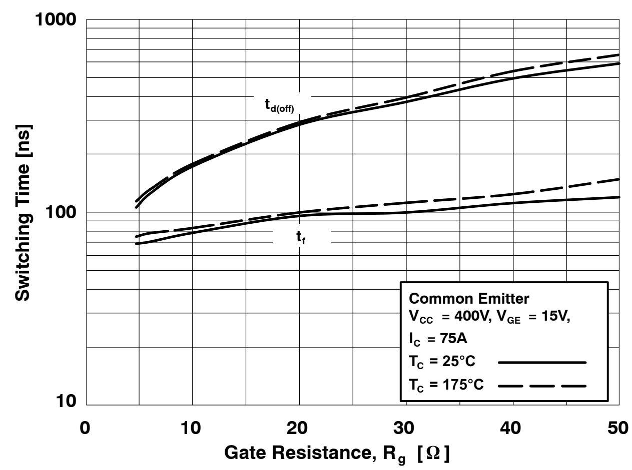


Figure 10. Turn−Off Characteristics vs. Gate Resistance

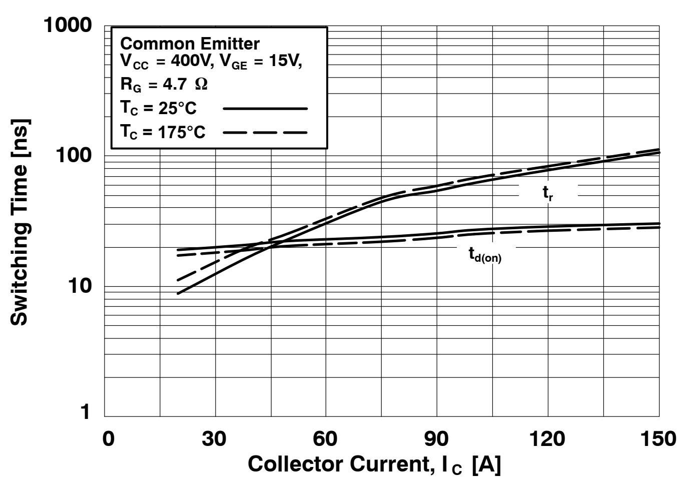


Figure 11. Turn−On Characteristics vs. Collector Current

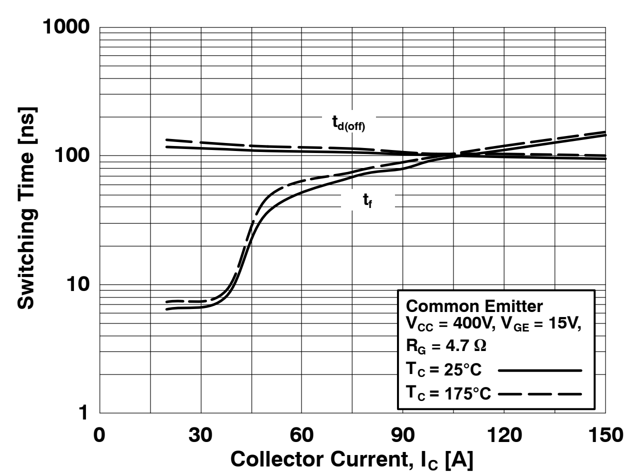


Figure 12. Turn−Off Characteristics vs. Collector Current

TYPICAL CHARACTERISTICS (continued)

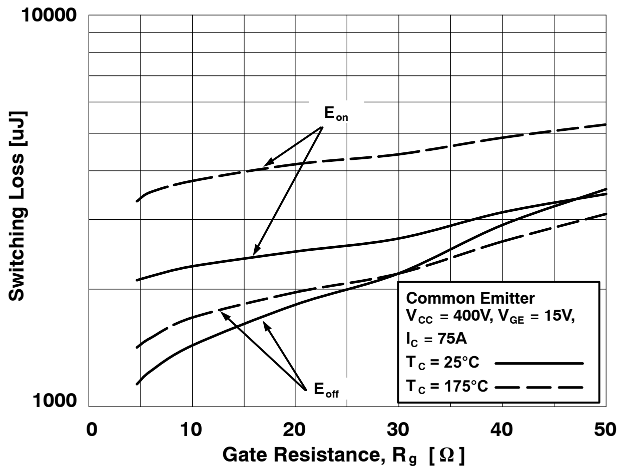


Figure 13. Switching Loss vs. Gate Resistance

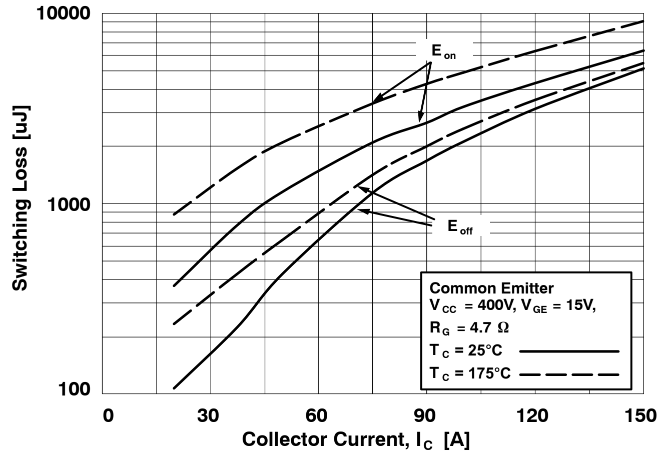


Figure 14. Switching Loss vs. Collector Current

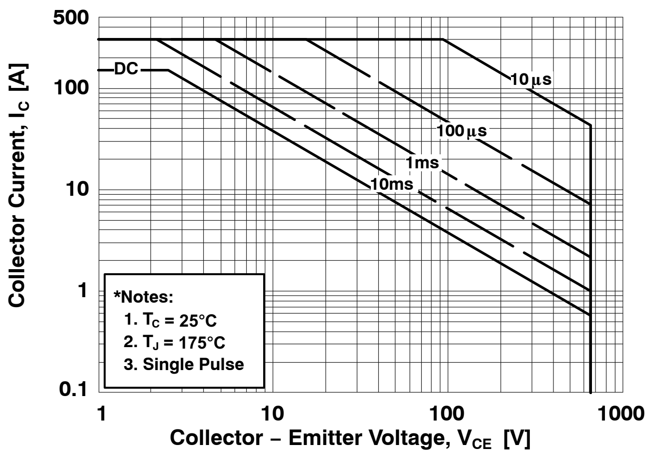


Figure 15. SOA Characteristics

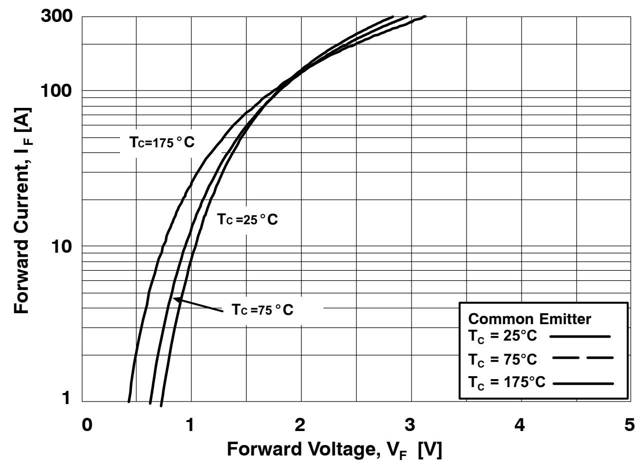


Figure 16. Forward Characteristics

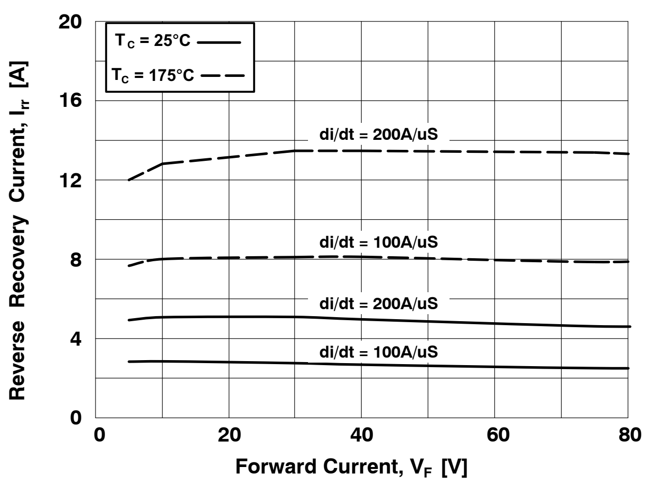


Figure 17. Reverse Recovery Current

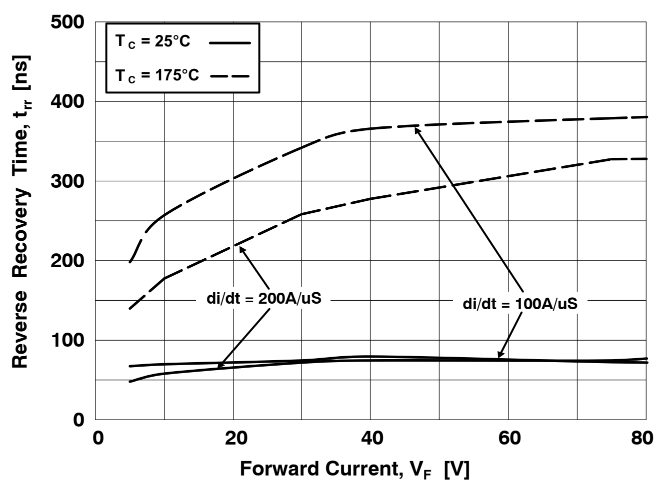


Figure 18. Reverse Recovery Time Stored Charge

TYPICAL CHARACTERISTICS (continued)

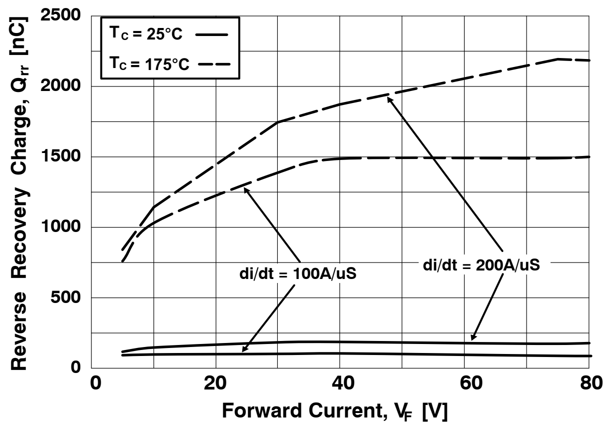


Figure 19. Stored Charge

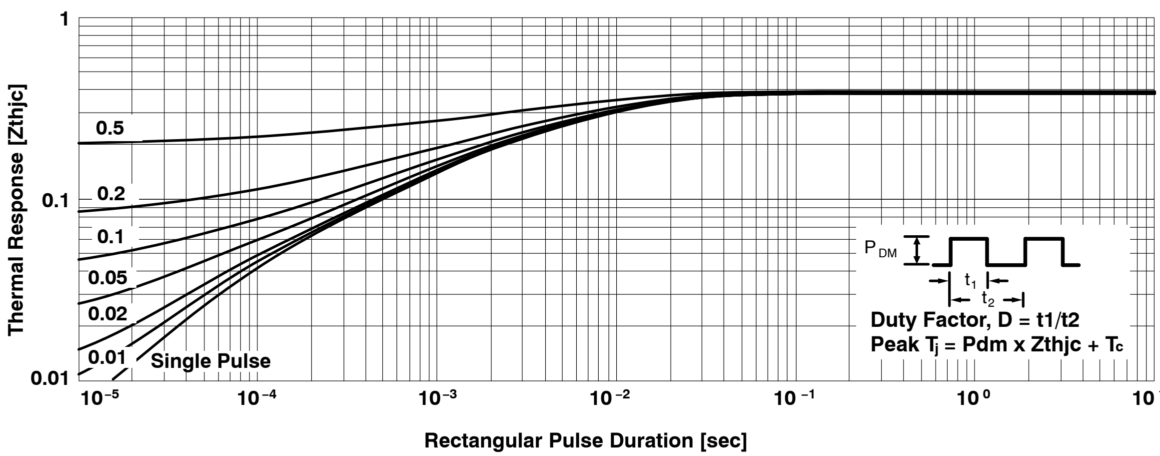


Figure 20. Transient Thermal Impedance of IGBT

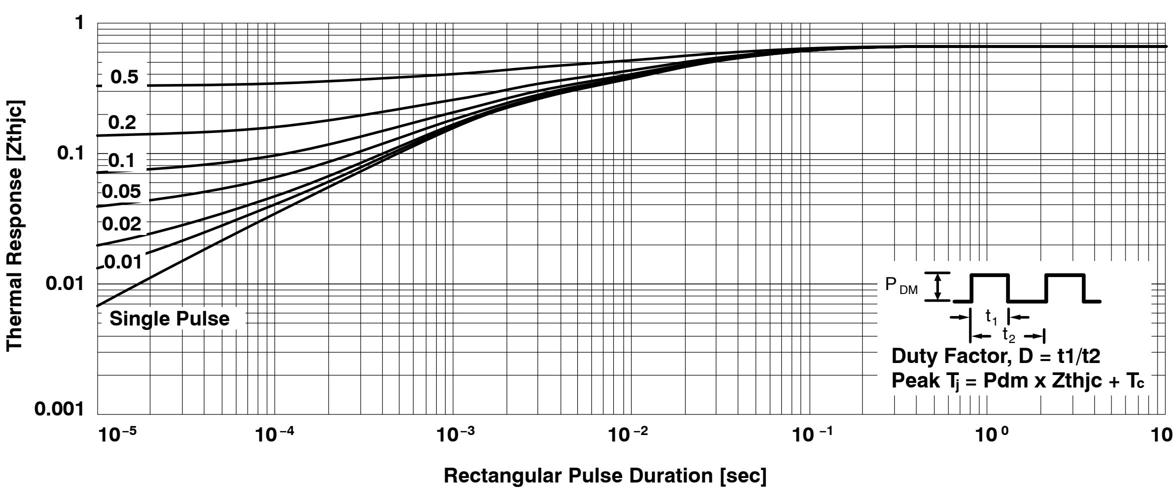
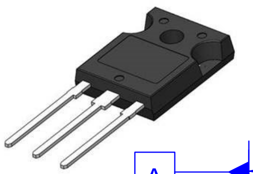
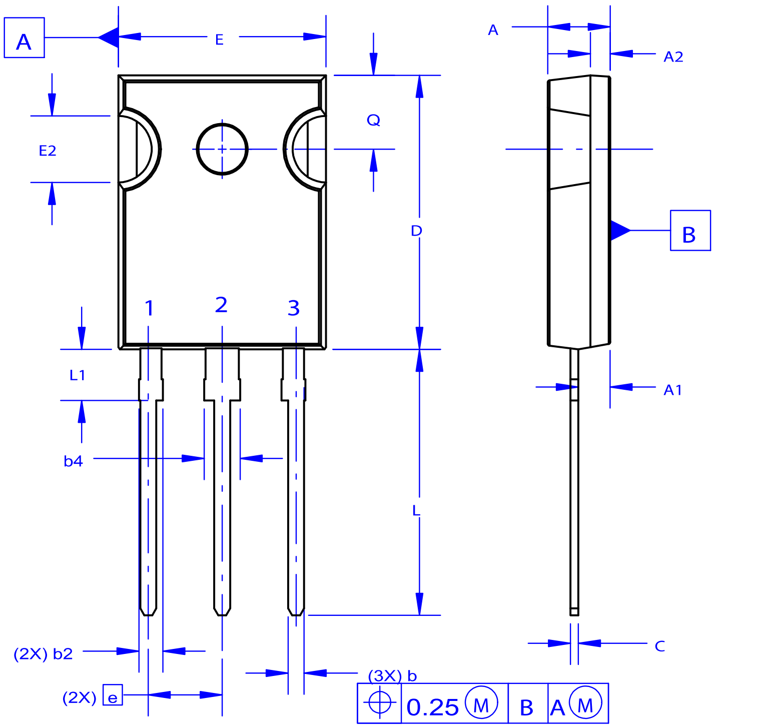


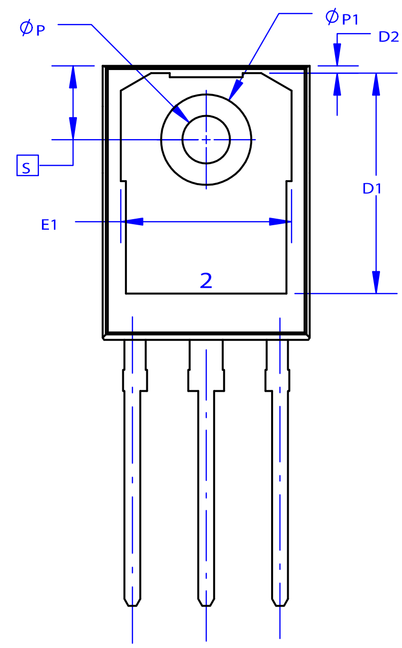
Figure 21. Transient Thermal Impedance of Diode



TO−247−3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020



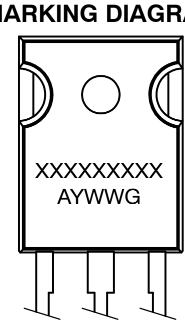


NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

GENERIC
MARKING DIAGRAM*



XXXXX	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present. Some products may not follow the Generic Marking.

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